

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	19	@ad<="20031229" and 'CMOS' and 'metal gate' same 'NMOS' and 'silicide gate' same 'PMOS'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 08:03
S2	1	"6506642".PN.	USPAT; USOCR	OR	ON	2005/02/25 13:30
S3	1	"6166417".PN.	USPAT; USOCR	OR	ON	2005/02/25 13:33
S4	1	"5949092".PN.	USPAT; USOCR	OR	ON	2005/02/25 13:38
S5	190	@ad<="20031229" and 'CMOS' and 'metal' with 'NMOS' and 'silicide' with 'PMOS'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/25 13:56
S6	75	@ad<="20031229" and 'CMOS' and 'metal gate' and 'silicide gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 09:25
S7	31	@ad<="20031229" and 'CMOS' and 'metal gate' same 'silicide gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/25 13:57
S8	1	"6586321".PN.	USPAT; USOCR	OR	ON	2005/02/25 14:00
S9	1	"6506642".PN.	USPAT; USOCR	OR	ON	2005/02/25 14:01
S10	1	"6475908".PN.	USPAT; USOCR	OR	ON	2005/02/25 14:01
S11	1	"6589836".PN.	USPAT; USOCR	OR	ON	2005/02/25 14:05
S12	1	"6294434".PN.	USPAT; USOCR	OR	ON	2005/02/25 14:06
S13	1	"6177335".PN.	USPAT; USOCR	OR	ON	2005/02/25 14:07
S14	1	"5122479".PN.	USPAT; USOCR	OR	ON	2005/02/25 14:07
S15	1	"5236872".PN.	USPAT; USOCR	OR	ON	2005/02/25 14:07
S16	14	@ad<="20031229" and 'NMOS' with 'metal gate' and 'PMOS' with 'silicide gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/25 14:36
S17	1	"6410376".PN.	USPAT; USOCR	OR	ON	2005/02/25 14:31

S18	1	"6274511".PN.	USPAT; USOCR	OR	ON	2005/02/25 14:33
S19	1	"6083836".PN.	USPAT; USOCR	OR	ON	2005/02/25 14:33
S20	1	"6051487".PN.	USPAT; USOCR	OR	ON	2005/02/25 14:34
S21	62	@ad<="20031229" and 'dual gate' with 'metal' with 'silicide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/25 14:37
S22	216	@ad<="20031229" and 'CMOS' and 'metal' same 'NMOS' and 'metal silicide' same 'PMOS'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/25 15:09
S23	85	@ad<="20031229" and 'CMOS' and 'metal' with 'NMOS' and 'metal silicide' with 'PMOS'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/25 15:59
S24	1	"6586321".PN.	USPAT; USOCR	OR	ON	2005/02/25 15:10
S25	1	"20020008294".PN.	US-PGPUB	OR	ON	2005/02/25 15:19
S26	1	"6410376".PN.	USPAT; USOCR	OR	ON	2005/02/25 15:20
S27	1	"6204103".PN.	USPAT; USOCR	OR	ON	2005/02/25 15:20
S28	1	"6204103".PN.	USPAT; USOCR	OR	ON	2005/02/25 15:20
S29	1	"5656519".PN.	USPAT; USOCR	OR	ON	2005/02/25 15:20
S31	0	@ad<="20031229" and 'polysilicon' same 'remove' and 'p-type polysicon' and 'n-type metal'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/25 16:03
S32	3	@ad<="20031229" and 'polysilicon' same 'remove' and 'p-type polysilicon' and 'n-type metal'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 08:22
S33	19	@ad<="20031229" and 'CMOS' and 'p-type polysilicon' and 'n-type metal'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 08:51
S34	1	"20020058374".PN.	US-PGPUB	OR	ON	2005/02/25 16:07
S35	1	"6586288".PN.	USPAT; USOCR	OR	ON	2005/02/25 16:07
S36	1	"6410376".PN.	USPAT; USOCR	OR	ON	2005/02/25 16:07

S37	1	"6365450".PN.	USPAT; USOCR	OR	ON	2005/02/25 16:07
S38	1	"6255698".PN.	USPAT; USOCR	OR	ON	2005/02/25 16:10
S39	1681	@ad<="20031229" and (257/410-413).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 08:04
S40	812	@ad<="20031229" and (257/310).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 08:04
S41	1589	@ad<="20031229" and (438/591-592).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 08:05
S42	956	@ad<="20031229" and (438/585).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 08:06
S43	554	@ad<="20031229" and (438/587-588).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 08:10
S44	680	@ad<="20031229" and (438/199).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 08:12
S45	508	@ad<="20031229" and (438/227-228).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 08:12
S46	1	@ad<="20031229" and 'NMOS' and 'PMOS' and 'p-type polysilicon' and 'remove' and 'n-type metal'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 09:26
S47	4	@ad<="20031229" and 'remove' and 'p-type polysilicon' and 'n-type metal'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 08:22
S48	2	"20040099916"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 08:27

S49	368	@ad<="20031229" and 'CMOS' and 'n-type' with 'metal' and 'p-type' with 'silicide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 09:29
S50	2	@ad<="20031229" and 'CMOS' and 'n-type metal' and 'p-type silicide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 09:29
S51	22	@ad<="20031229" and 'CMOS' and 'n-type' with 'metal' and 'p-type' with 'cobalt silicide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 10:32
S52	4	@ad<="20031229" and 'CMOS' and 'n-type' with 'metal' same 'p-type' with 'cobalt silicide' same 'gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 09:30
S53	4	@ad<="20031229" and 'CMOS' and 'n-type' with 'metal' same 'p-type' with 'cobalt silicide' same 'electrode'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 09:30
S54	48	@ad<="20031229" and 'hafnium oxide' same 'atomic' with 'cvd'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 10:34
S55	10	@ad<="20031229" and 'hafnium oxide' with 'atomic' with 'cvd'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 10:52
S56	0	brask-justin.in. and 'intel'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 10:52
S57	0	brask-justin.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 10:53
S58	12	'brask justin' and 'Intel'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 11:01
S59	12	'brask' adj1 'justin' and 'Intel'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 10:07

S60	19	@ad<="20031229" and 'CMOS' and 'p-type polysilicon' and 'n-type metal'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 11:17
S61	53	@ad<="20031229" and 'CMOS' and 'polysilicon' with 'silicide' and 'n-type metal'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 09:13
S62	1	"20020058374".PN.	US-PGPUB	OR	ON	2005/04/19 08:52
S63	1	"6586288".PN.	USPAT; USOCR	OR	ON	2005/04/19 09:05
S64	1	"6410376".PN.	USPAT; USOCR	OR	ON	2005/04/19 09:05
S65	1	"6365450".PN.	USPAT; USOCR	OR	ON	2005/04/19 09:06
S66	1	"6255698".PN.	USPAT; USOCR	OR	ON	2005/04/19 09:07
S68	533	@ad<="20031229" and 'CMOS' same 'silicide' with 'metal' with 'gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 09:14
S69	82	@ad<="20031229" and 'CMOS' and 'metal gate' and 'silicide gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 09:42
S70	864	@ad<="20031229" and 'CMOS' same 'dual gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 09:43
S71	103	@ad<="20031229" and 'CMOS' same 'dual gate' and 'work function'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 09:43
S72	1	"6200866".PN.	USPAT; USOCR	OR	ON	2005/04/19 09:53
S73	1	"6033963".PN.	USPAT; USOCR	OR	ON	2005/04/19 09:53
S74	1	"5966597".PN.	USPAT; USOCR	OR	ON	2005/04/19 09:53
S75	1	"5960270".PN.	USPAT; USOCR	OR	ON	2005/04/19 09:53
S76	16	'brask' adj1 'justin' and 'Intel'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 10:09

S77	29	chau-robert.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 10:12
S78	12	thomas-christopher.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 10:13
S79	13	datta-suman.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 10:13
S80	419	@ad<="20031229" and 'CMOS' and 'p-type polysilicon' and 'n-type polysilicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 10:38
S81	22	@ad<="20031229" and 'CMOS' and 'p-type polysilicon' and 'n-type polysilicon' and 'selective etching'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 10:47
S82	31	@ad<="20031229" and 'p-type polysilicon' and 'n-type polysilicon' and 'selective etch'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 11:05
S83	0	cha-liang-cher.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 11:06
S84	0	cher-liang-cha.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 11:06
S85	0	cha-liang.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 11:06
S86	3	'cher liang cha' and 'chartered semiconductor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 11:31
S87	59	@ad<="20031229" and 'CMOS' and 'p-type polysilicon' with 'silicide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 11:17

S88	315	@ad<="20031229" and 'CMOS' and 'chartered semiconductor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 11:31
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